## Inverter Sizing

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## Load capacitances



## Inverter Delay

- Minimum length devices, $L=0.25 \mu \mathrm{~m}$
- Assume that for $W_{P}=2 W_{N}=2 W$
- same pull-up and pull-down currents
- approx. equal resistances $\boldsymbol{R}_{N}=\boldsymbol{R}_{P}$
- approx. equal rise $t_{p L H}$ and fall $t_{p H L}$ delays
- Analyze as an RC network


Delay $(D): t_{p H L}=(\ln 2) R_{N} C_{L} \quad t_{p L H}=(\ln 2) R_{P} C_{L}$
Load for the next stage: $C_{g i n}=3 \frac{W}{W_{u n i t}} C_{\text {unit }}$
$W_{u n i t}$ and $C_{u n i t}$ correspond to an unit size (minimum size) gate...

## Inverter with Load



Assumptions: no load $\longrightarrow$ zero delay?

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## Inverter with Load



Delay $\left(\mathrm{t}_{\mathrm{p}}\right)=k R_{W}\left(C_{\text {int }}+C_{e x t}\right)=k R_{W} C_{\text {int }}+k R_{W} C_{\text {ext }}=\frac{k R_{W} C_{i n t}\left(1+C_{\text {ext }} / C_{i n t}\right)}{\downarrow}$ $t_{p o}$ (intrinsic delay)

## Intrinsic delay of CMOS inverter

Let $R_{\text {eq }}$ be the equivalent resistance of the gate (inverter), then delay $\left(t_{p}\right)$ is defined as:

$$
\begin{aligned}
& t_{p}=0.69 R_{e q}\left(C_{i n t}+C_{e x t}\right) \\
& =0.69 R_{e q} C_{i n t}\left(1+\frac{C_{e x t}}{C_{i n t}}\right) \\
& =t_{p 0}\left(1+\frac{C_{e x t}}{C_{i n t}}\right)
\end{aligned}
$$

$t_{p 0}$ is the intrinsic delay

## Impact of sizing on gate delay

Let $S$ be the sizing factor
$R_{\text {ref }}$ be the resistance of a reference gate (usually a minimum size gate)
$C_{\text {iref }}$ be the internal capacitance of the reference gate

$$
\begin{aligned}
C_{\text {int }} & =S C_{\text {iref }}, \quad R_{e q}=\frac{R_{r e f}}{S} \\
t_{p} & =0.69\left(\frac{R_{r e f}}{S}\right)\left(S C_{\text {iref }}\right)\left(1+\frac{C_{\text {ext }}}{S C_{\text {iref }}}\right) \\
& =0.69 R_{\text {ref }} C_{\text {iref }}\left(1+\frac{C_{\text {ext }}}{S C_{\text {iref }}}\right) \\
& =t_{p 0}\left(1+\frac{C_{\text {ext }}}{S C_{\text {iref }}}\right)
\end{aligned}
$$

Hence:

1. Intrinsic delay is independent of gate sizing, and is determined only by technology and inverter layout
2. If $S$ is made very large, gate delay approaches the intrinsic value but increases the area significantly

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## Inverter Chain



If $C_{L}$ is given:

- How many stages are needed to minimize the delay?
- How to size the inverters?

May need some additional constraints....

## Delay Formula: inverter chain

$$
\text { Delay } \sim R_{e q}\left(C_{i n t}+C_{e x t}\right)
$$

$$
\begin{aligned}
& t_{p}=\underbrace{0.69 R_{e q} C_{i n}}\left(1+C_{\text {ext }} / \gamma C_{\text {gin }}\right)=t_{p 0}(1+f / \gamma) \\
& t_{p 0} \begin{array}{l}
\text { relates the input gate cap. and the } \\
\text { intrinsic output cap. of the inverter... } C_{\text {int }}=\gamma C_{\text {gin }} \text { with } \gamma \approx 1 \\
f=C_{\text {ext }} / C_{\text {gin }}-\text { effective fanout }
\end{array}
\end{aligned}
$$

## Apply to Inverter Chain



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## Optimal Tapering for Given N

Delay equation has $N-1$ unknowns, $C_{g, 2} \ldots C_{g, N}$
Minimize the delay, find $N-1$ partial derivatives and equate them to zero, or $\left(\partial_{t_{p}} / \partial c_{g, j}\right)=0$
Result: $C_{g, j+1} / C_{g, j}=C_{g, j} / C_{g, j-1}$ With $\mathrm{j}=2, \ldots ., \mathrm{N}$
Size of each stage is the geometric mean of two neighbors

$$
C_{g, j}=\sqrt{C_{g, j-1} C_{g, j+1}}
$$

- each stage has the same effective fanout ( $f_{j}=f=C_{e x i} / C_{g, j}$ )
- hence, each stage has the same delay: $\mathrm{t}_{\mathrm{p}}=\mathrm{t}_{\mathrm{po}}(1+\mathrm{f} / \gamma)$


## Optimum Delay and Number of Stages

When each stage is sized by $f$ and has same eff. fanout $f$ :
$\frac{C_{L}}{C_{g, N}}=\frac{C_{g, N}}{C_{g, N-1}}=\cdots \cdots \cdots=\frac{C_{g, 2}}{C_{g, 1}}=f$
Hence, $f^{N}=C_{L} / C_{g, 1}=F \quad \begin{aligned} & \text { Fis the overall effective fanout of the } \\ & \text { circuit }\end{aligned}$
Effective fanout of each stage: $\quad f=\sqrt[N]{F} \quad$ If $c_{L}$ and $C_{g, 1}$ are known....

## Minimum path delay:

$$
\begin{gathered}
t_{p}=N t_{p 0}(1+\sqrt[N]{F} / \gamma) \\
\text { How to choose } N \text { ? }
\end{gathered}
$$

If $N$ is too large, intrinsic delay of stages dominate, while if $N$ is small, effective fanout of each stage (f) is large and the second term dominates

## Example

## If $N$ is given....


$C_{L} / C_{1}$ has to be evenly distributed across $N=3$ stages:

$$
f=\sqrt[3]{8}=2
$$

## Optimum Number of Stages

For a given load, $C_{L}$ and given input capacitance $C_{\text {in }}$ Find optimal sizing $f$

$$
\begin{gathered}
C_{L}=F \cdot C_{\text {in }}=f^{N} C_{\text {in }} \text { with } N=\frac{\ln F}{\ln f} \\
t_{p}=N t_{p 0}\left(F^{1 / N} / \gamma+1\right)=\frac{t_{p 0} \ln F}{\gamma}\left(\frac{f}{\ln f}+\frac{\gamma}{\ln f}\right) \\
\frac{\partial t_{p}}{\partial f}=\frac{t_{p 0} \ln F}{\gamma} \cdot \frac{\ln f-1-\gamma / f}{\ln ^{2} f}=0
\end{gathered}
$$

If self-loading is ignored....
For $\gamma=0, f=\mathrm{e}=2.718, N=\ln F$

Otherwise....

$$
f=\exp (1+\gamma / f)
$$

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## Optimum Effective Fanout f

Optimum $f$ for given process defined by $\gamma$

$$
f=\exp (1+\gamma / f)
$$



$$
\begin{aligned}
& \begin{array}{l}
\text { Optimum } \\
\text { tapering factor: } \\
f_{\text {opt }}=3.6 \\
\text { for } \gamma=1 \text { (typical case) }
\end{array}
\end{aligned}
$$

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## Impact of Self-Loading on tp

No Self-Loading, $\gamma=0$


Optimal number of stages, $N=\ln (F)$

With Self-Loading $\gamma=1$


If $f<f_{\text {opt }}$ (too many stages) will result in delay to increase

## Normalized delay function of F

$$
t_{p}=N t_{p 0}(1+\sqrt[N]{F} / \gamma)
$$

$$
t_{\text {popt }} / t_{p o} \text { for } \gamma=1
$$

| $F$ | Dibutiered | Tumstine | Imerierchain |
| :---: | :---: | :---: | :---: |
| 10 | 11 | 8.3 | 8. 3 |
| 16 | 141 | 22 | 16.5 |
| 16 O | 1-1)-1 | 0 | 24.8 |
| 10¢0] | 10,401 | 202 | 33.1 |

As Fincreases, the differences between the unbuffered case (or two-stage buffer case) and the case of inverter chain increases.....

## Buffer Design

$f=F^{1 N}$

| N | f | $\mathrm{t}_{\mathrm{p}}$ |
| :--- | :--- | :--- |
| 1 | 64 | 65 |
| 2 | 8 | 18 |
|  |  |  |
| 3 | 4 | 15 |
|  |  |  |
| 4 | 2.8 | 15.3 |

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## Sizing Logic Paths for Speed

$\square$ Frequently, input capacitance of a logic path is constrained

- Logic also has to drive some capacitance
- Example: ALU load in an Intel's microprocessor is 0.5 pF
- How do we size the ALU datapath to achieve maximum speed?
- We have already solved this for the inverter chain - can we generalize it for any type of logic?


## Buffer Example

 (in units of $\tau_{i n v}$ )

For given $N: C_{g, j+1} / C_{g, j}=C_{g, j} / C_{g, j-1}$
Optimal fanout (f): $C_{g, j+1} / C_{g, j} \sim 4$
How to generalize this to any logic path?

## Minimizing Delay in Complex

## Logic Networks

$$
\begin{aligned}
& \text { Delay }=t_{p 0}\left(1+\frac{f}{\gamma}\right)(\text { inverter }) \\
& =t_{p 0}\left(p+\frac{g \cdot f}{\gamma}\right)(\text { Complexgate })
\end{aligned}
$$

Everything Normalized w.r.t an inverter:
$g_{i n v}=1, p_{i n v}=1$
$f$ - effective fanout (ratio of external load and input cap. of gate)
$p$ - ratio of intrinsic delays of complex gate and inverter
(value increases with complexity of gate)
$g$ - logical effort: how much more input capacitance is presented by the complex gate to deliver the same output current as an inverter (depends only on circuit topology)

## Logical Effort

- Inverter has the smallest logical effort and intrinsic delay of all static CMOS gates
- Logical effort of a gate is the ratio of its input capacitance to the inverter capacitance when sized to deliver the same current
- Logical effort increases with gate complexity


## Logical Effort

## Logical effort is the ratio of input capacitance of a gate to the input capacitance of an inverter with the same output current



Inverter
$g=1$


2-input NAND
$g=4 / 3$


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## Delay in a Logic Gate

## Gate delay:



Effort delay (or gate effort):
logical effort effective fanout $=C_{\text {ext }} / C_{\text {in }}$
$>$ Logical effort is a function of topology, independent of sizing $>$ Effective fanout (electrical effort) is a function of load/gate size

## Logical Effort of Gates


$>$ Delay can be adjusted by:
> transistor sizing that changes the effective fanout
> Choosing a gate with different $g$

## Logical Effort of Gates



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## Logical Effort

|  | Number of Inputs |  |  |  |
| :--- | :---: | :---: | :---: | :---: |
| Gate Type | $\mathbf{1}$ | $\mathbf{2}$ | $\mathbf{3}$ | $\mathbf{n}$ |
| Inverter | 1 |  |  |  |
| NAND | $4 / 3$ | $5 / 3$ | $(2 n+2) / 3$ |  |
| NOR | $5 / 3$ | $7 / 3$ | 2 |  |
| Multiplexer | 2 | 2 |  |  |
| XOR | 4 | 12 |  |  |

From Sutherland, Sproull

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## Total delay through a combinational

 logic block$$
t_{p}=\sum_{j=1}^{N} t_{p, j}=t_{p 0} \sum_{j=1}^{N}\left(p_{j}+\frac{f_{j} g_{j}}{\gamma}\right)
$$

Similar to inverter chain delay....find N-1 partial derivatives and equate them to zero....

For minimal delay : $g_{1} f_{1}=g_{2} f_{2}=\ldots=g_{N} f_{N}$ (each stage should have the same gate effort, h)

$$
\text { PathLogic Effort }=G=\prod_{1}^{N} g_{i}
$$

Note: In the text book, this is defined as H

$$
\underset{\text { Path Effective Fanout }=F=}{ }=\frac{C_{L}}{C_{g 1}}
$$

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## Branching Effort

To relate F to the effective fanouts of the individual gates, one must account for the logical fanout within the network

When fanout occurs at the output of a node, some of the available drive current is directed along the path being analyzed

Branching effort of a logic gate:

$$
b=\frac{C_{\text {on-path }}+C_{\text {off }- \text { path }}}{C_{\text {on-path }} \longleftarrow} \text { ( Load capacitance of } \begin{gathered}
\text { the gate along the } \\
\text { path under study }
\end{gathered}
$$



$$
\text { PathBranchingEffort }=B=\prod_{1}^{N} b_{i}
$$

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## Total Path Effort

- Path electrical effort can be related to the electrical and branching efforts of the individual gates:

$$
F=\prod_{1}^{N} \frac{f_{i}}{b_{i}}=\frac{\prod f_{i}}{B}
$$

- Total path effort can be defined as:

$$
H=\prod_{1}^{N} h_{i}=\prod_{1}^{N} g_{i} f_{i}=G F B \quad \begin{aligned}
& \text { Note: In the text book, H and } \\
& \text { F have been swapped... }
\end{aligned}
$$

- Gate effort that minimizes the path delay = ?
- Minimum delay through path = ?


## Multistage Networks

$$
\text { Delay }=\sum_{i=1}^{N}\left(p_{i}+g_{i} \cdot f_{i}\right)
$$

Gate effort: $h_{i}=g_{i} f_{i}$
Path electrical effort: $F=C_{L} / C_{\text {gin }}$
Path logical effort: $G=g_{1} g_{2} \ldots g_{N}$
Path branching effort: $B=b_{1} b_{2} \ldots b_{N}$
*Path effort: $H=G F B$
Path delay $D=\Sigma d_{i}=\Sigma p_{i}+\Sigma h_{i}$

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## Optimal Number of Stages

For a given load, and given input capacitance of the first gate Find optimal number of gates and optimal sizing

$$
\begin{gathered}
D=N H^{1 / N}+N p_{i n v} \\
\frac{\partial D}{\partial N}=-H^{1 / N} \ln \left(H^{1 / N}\right)+H^{1 / N}+p_{i n v}=0
\end{gathered}
$$

Substitute 'best gate effort': $\quad h=H^{1 / N} \Rightarrow \begin{aligned} & \text { Ginimizes path delay }\end{aligned}$
A path achieves least delay by using $N=\log _{4} H$ stages

## Optimum Effort per Stage

When each stage bears the same effort:

$$
\begin{aligned}
& h^{N}=H \\
& h=\sqrt[N]{H}
\end{aligned}
$$

gate efforts: $g_{1} f_{1}=g_{2} f_{2}=\ldots=g_{N} f_{N}$
Effective fanout of each gate: $f_{i}=h / g_{i}$
Minimum path delay:

$$
D=t_{p 0}\left(\sum_{j=1}^{N} p_{j}+\frac{N(\sqrt[N]{H})}{\gamma}\right)
$$

## Sizing of Chain of Gates

- Consider chain $\mathrm{s}_{\mathrm{i}}$
- Sizing factors for each gate in the chain can be derived by working out from front to end (or vice versa).
- Assume that a unit-size gate has a driving capability equal to a minimum-size inverter
- Hence, $C_{g i n}=\mathrm{g} \mathrm{C}_{\text {in_ref }}$
- If $s_{1}$ is the sizing factor for gate 1 :
- $\mathrm{C}_{\mathrm{g} 1}=\mathrm{s}_{1} \mathrm{~g}_{1} \mathrm{C}_{\text {in_ref }}$
- Input capacitance of gate 2 is larger by $f_{1} / b_{1}$ :

That is, $\mathrm{C}_{\mathrm{g} 2}=\mathrm{f}_{1} / \mathrm{b}_{1} \mathrm{C}_{\mathrm{g} 1}=\mathrm{s}_{2} \mathrm{~g}_{2} \mathrm{C}_{\text {in_ref }}$

- For gate i in the chain:

$$
s_{i}=\left(\frac{g_{1} s_{1}}{g_{i}}\right) \prod_{j=1}^{i-1}\left(\frac{f_{j}}{b_{j}}\right)
$$

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## Example: Optimize Path



## Example: Optimize Path



Effective fanout, $F=5 / 1=5$
$G=1 \times 5 / 3 \times 5 / 3 \times 1=25 / 9$
$B=1$ (no branching)
$H=G F B=125 / 9=13.9$
$h=\mathrm{H}^{1 / 4}=1.93$ (optimal gate effort)
Derive Fanout Factors (taking gate types into account): $f 1=1.93$ (since h=gf)
$f 2=1.93(3 / 5)=1.16$
$f 3=1.16$
$f 4=1.93$

## Example - 8-input AND



## Method of Logical Effort

- Compute the path effort: $H=G F B$
$\square$ Find the best number of stages $N \sim \log _{4} H$
- Compute the stage effort $h=H^{1 / N}$
$\square$ Sketch the path with this number of stages
$\square$ Work from either end, find sizes:
$C_{\text {in }}=C_{\text {out }}{ }^{*} g / h$

Reference: Sutherland, Sproull, Harris, "Logical Effort, Morgan-Kaufmann 1999.

Table 4: Key Definitions of Logical Effort

| Term | Stage expression | Path expression |
| :--- | :---: | :---: |
| Logical effort | $g$ | $G=\prod g_{i}$ |
| Electrical effort | $f=\frac{C_{\text {out }}}{C_{\text {in }}}$ | $F=\frac{C_{\text {out (path) }}}{C_{\text {in (path) }}}$ |
| Branching effort | n/a | $B=\prod b_{i}$ |
| Effort | $h=g f$ | $H=G F B$ |
| Effort delay | $h$ | $D_{H}=\sum h_{i}$ |
| Number of stages | 1 | $N$ |
| Parasitic delay | $p$ | $P=\sum p_{i}$ |
| Delay | $d=h+p$ | $D=D_{H}+P$ |

Sutherland, Sproull and Harris

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[^0]:    * Note: In the text book, this is defined as: F = GHB

